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a third conductor including a first wire formed on said first insulating film and the first plug and a second wire formed on an extension of the first wire on said first insulating film and the second plug; and

what?
extension

a second insulating film formed on said third conductor and over said first insulating film, said second insulating film including a thin area over said second conductor for guiding a laser beam.

2. (Amended) The semiconductor device of claim 1, wherein:

said second conductor includes a third plug and a fourth plug formed on said first conductor through said first insulating film; and

said third conductor includes a third wire formed parallel with the first wire on said first insulating film and the third plug and a fourth wire formed on an extension of the third wire on said first insulating film and the fourth plug.

5. (Amended) The semiconductor device of claim 2, wherein:

said second conductor includes a fifth plug formed on a first straight line (12)
connecting the first plug and the third plug on said first conductor through said first insulating film and a sixth plug formed on a second straight line (1213) connecting the second plug and the fourth plug on said first conductor through said first insulating film.

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16. (Amended) The semiconductor device of claim 1, wherein:

the second conductor includes a first portion formed on said first conductor and a second portion formed on the first portion made of a different material from that of the first portion.

Please add new claims 30-44, as follows:

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30. (New) A semiconductor device comprising:

a first insulating film;
a first lower wire formed on said first insulating film;
a second insulating film formed on said first lower wire;
a first conductor formed through said second insulating film including a first portion formed on said first lower wire and a second portion formed on the first portion made of a different material from that of the first portion;

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a first upper wire formed parallel with said first lower wire on said second insulating film and said first conductor; and

a third insulating film formed on said first upper wire and over said second insulating film, said third insulating film including a thin area over said first conductor for guiding a laser beam.

31. (New) The semiconductor device of claim 30, further comprising:

a second lower wire formed ~~on an extension of said~~ first lower wire on said first insulating film beneath said second insulating film;

a second conductor formed through said second insulating film below the thin area including a third portion formed on said second lower wire made of a same material as the first portion and a fourth portion formed on the third portion made of a same material as the second portion; and

a second upper wire formed parallel with said second lower wire on said second insulating film and said second conductor beneath said third insulating film.

32. (New) The semiconductor device of claim 30, wherein said first lower wire is obliquely below said first upper wire.

33. (New) A semiconductor device comprising:

a semiconductor substrate;
a first insulating film formed on said semiconductor substrate;
a first conductor formed on said semiconductor substrate through said first insulating film;
a first upper wire formed on said first insulating film and said first conductor; and
a second insulating film formed on said first upper wire and over said first insulating film, said second insulating film including a thin area over said first conductor for guiding a laser beam.

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34. (New) The semiconductor device of claim 33, further comprising:
a second conductor formed on said semiconductor substrate through said first insulating film below the thin area; and
a second upper wire formed on an extension of said first upper wire on said first insulating film and said second conductor beneath said second insulating film.

35. (New) The semiconductor device of claim 33, wherein
said first conductor includes a first portion formed on said semiconductor substrate and a second portion formed on the first portion made of a different material from that of the first portion.

36. (New) A semiconductor device comprising:
a semiconductor substrate;
a first insulating film formed on said semiconductor substrate;
first conductors formed on said semiconductor substrate through said first insulating film;

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first upper wires formed on said first insulating film and said first conductors alternated on two parallel lines such that ends of said first upper wires on one of the parallel lines oppose ends of said first upper wires on the other of the parallel lines; and a second insulating film formed on said first upper wires and over said first insulating film, said second insulating film including a thin area over said first conductors for guiding a laser beam.

37. (New) The semiconductor device of claim 36, wherein
said first conductors include first portions formed on said semiconductor
substrate and second portions formed on the first portions made of a different material
from that of the first portions.

38. (New) A semiconductor device comprising:
a first insulating film;
first lower wires formed on said first insulating film alternated on two parallel lines such that ends of said first lower wires on one of the parallel lines oppose ends of said first lower wires on the other of the parallel lines;
a second insulating film formed on said first lower wires;
first conductors formed on said first lower wires through said second insulating film;
first upper wires formed parallel with said first lower wires on said second insulating film and said first conductors; and
a third insulating film formed on said first upper wires and over said second insulating film, said third insulating film including a thin area over said first conductors for guiding a laser beam.

39. (New) The semiconductor device of claim 38, wherein
said first conductors include first portions formed on said first lower wires and
second portions formed on the first portions made of a different material from that of the
first portions.

40. (New) The semiconductor device of claim 38, wherein said first lower wires
are obliquely below said first upper wires being able to conduct to said first lower wires.

41. (New) A semiconductor device comprising:
a first insulating film;
a first lower wire formed on said first insulating film;
a second insulating film formed on said first lower wire;
a first conductor formed on said first lower wire through said second insulating
film;
a second conductor formed on said first lower wire through said second
insulating film;
a first upper wire formed on said second insulating film and said first conductor;
a second upper wire formed parallel with said first upper wire on said second
insulating film and said second conductor; and
a third insulating film formed on said first upper wire and said second upper wire
and over said second insulating film, said third insulating film including a thin area over
said first conductor and said second conductor for guiding a laser beam.

42. (New) The semiconductor device of claim 41, further comprising:
a second lower wire formed parallel with said first lower wire on said first
insulating film beneath said second insulating film;

a third conductor formed on said second lower wire below the thin area through said second insulating film;

a fourth conductor formed on said second lower wire below the thin area through said second insulating film;

a third upper wire formed on an extension of said first upper wire on said second insulating film and said third conductor beneath said third insulating film; and

a fourth upper wire formed on an extension of said second upper wire on said second insulating film and said fourth conductor beneath said third insulating film;

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43. (New) The semiconductor device of claim 41, wherein said first conductor includes a first portion formed on said first lower wire and a second portion formed on the first portion made of a different material from that of the first portion.

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44. (New) The semiconductor device of claim 42, wherein
said first, second, third and fourth upper wires are alternated ^{2nd line} on two parallel lines
such that ends of said first and second upper wires on one of the parallel lines oppose
ends of said third and fourth upper wires on the other of the parallel lines.

IN THE DRAWINGS:

Subject to the approval of the Examiner, please amend Figs. 1A to 1C by including the legend --Prior Art--, as shown in the accompanying Request for Approval of Drawing Change.

REMARKS

By this Amendment, Applicants cancel claims 3 and 4 without prejudice or disclaimer of the subject matter thereof, amend claims 1, 2, 5, and 16, and add new claims 30-44. Thus, claims 1, 2, and 5-44 remain pending.